Silicon NPN Power Transistors MJE13003

DESCRIPTION

- With TO-126 package
- High voltage ,high speed

APPLICATIONS

- Particularly suited for 115V and 220V switchmode applications such as switching regulators,inverters ,motor controls,solenoid/ relay drivers and deflection circuits

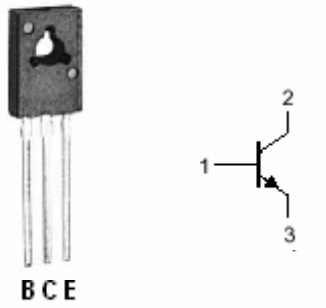

Fig.1 simplified outline (TO-126) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings (Tc=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	700	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	9	V
I_C	Collector current (DC)		1.5	A
I_{CM}	Collector current-Peak		3	A
I_B	Base current		0.75	A
I_{BM}	Base current-Peak		1.5	A
I_E	Emitter current		2.25	A
I_{EM}	Emitter current-Peak		4.5	A
P_D	Total power dissipation	T_a=25℃	1.4	W
		T_C=25℃	40	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance from junction to case	3.12	℃/W

Silicon NPN Power Transistors MJE13003

CHARACTERISTICS

Tj=25℃ unles otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=10mA ;I_B=0	400			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=0.5A; I_B=0.1A			0.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=1A; I_B=0.25A T_C=100℃			1.0 1.0	V
$V_{CEsat-3}$	Collector-emitter saturation voltage	I_C=1.5A;I_B=0.5A			3.0	V
$V_{BEsat-1}$	Base-emitter saturation voltage	I_C=0.5A; I_B=0.1A			1.0	V
$V_{BEsat-2}$	Base-emitter saturation voltage	I_C=1A; I_B=0.25A T_C=100℃			1.2 1.1	V
I_{CEV}	Collector cut-off current	V_{CEV}=Rated value; $V_{BE\ (off)}$ =1.5V T_C=100℃			1.0 5.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=9V; I_C=0			1.0	mA
h_{FE-1}	DC current gain	I_C=0.5A ; V_{CE}=2V	8		40	
h_{FE-2}	DC current gain	I_C=1A ; V_{CE}=2V	5		25	
f_T	Transition frequency	I_C=0.1A ; V_{CE}=10V;f=1MHz	4			MHz
C_{OB}	Collector outoput capacitance	I_E=0;f=0.1MHz ; V_{CB}=10V		21		pF

Switching times resistive load

t_d	Delay time	V_{CC}=125V ,I_C=1A I_{B1}=-I_{B2}=0.2A t_p=25μs duty cycle≤1%		0.05	0.1	μs
t_r	Rise time			0.5	1.0	μs
t_s	Storage time			2.0	4.0	μs
t_f	Fall time			0.4	0.7	μs

PACKAGE OUTLINE

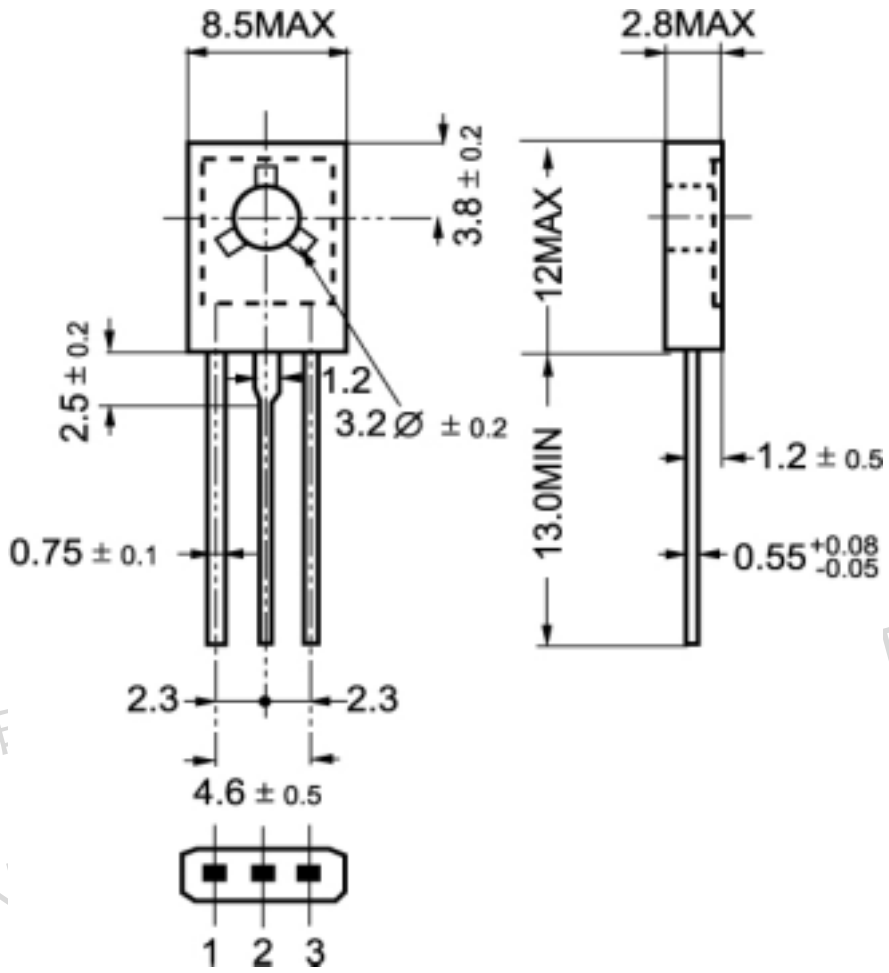

Fig.2 Outline dimensions

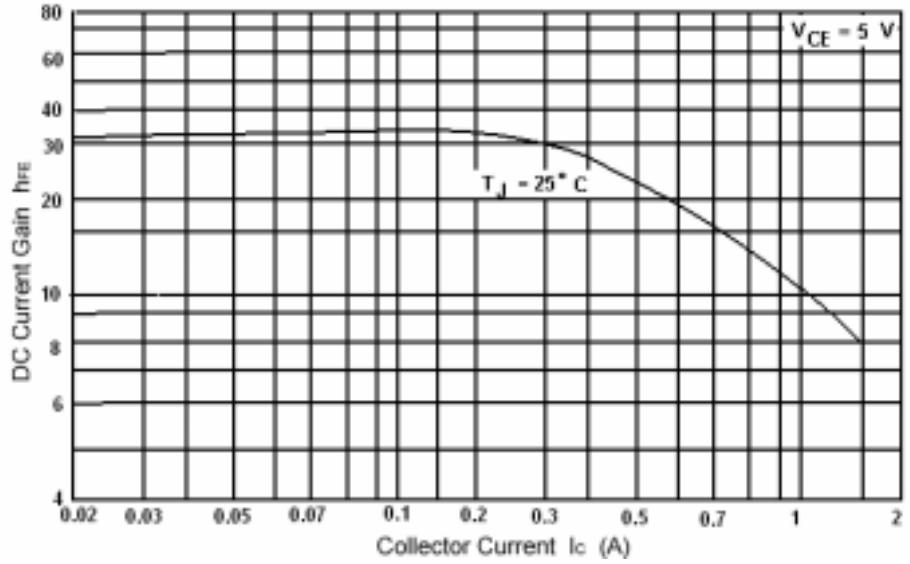

Fig.3 DC current Gain

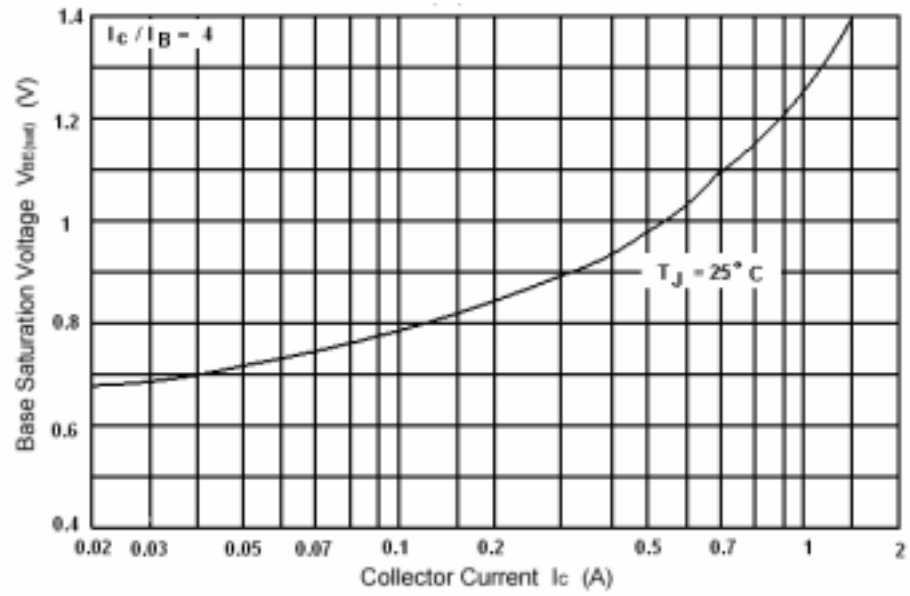

Fig.4 Base-Emitter Saturation Voltage

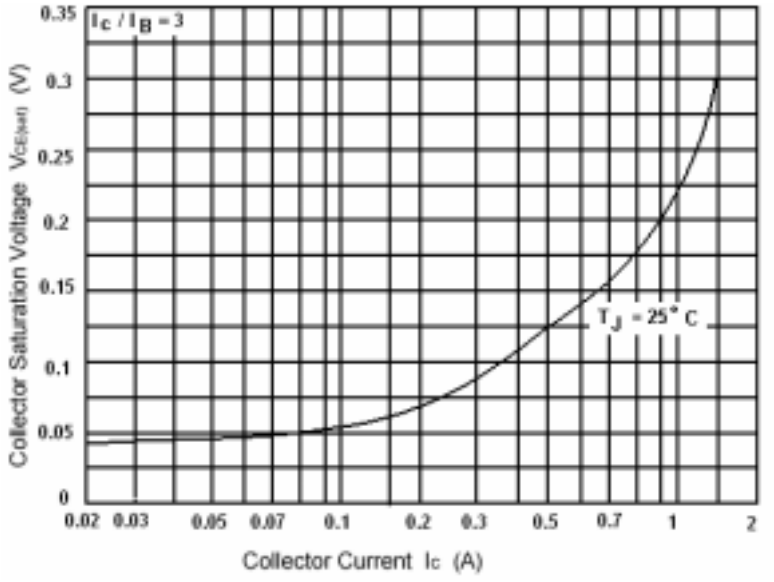

Fig.5 Collector-Emitter Saturation Voltage

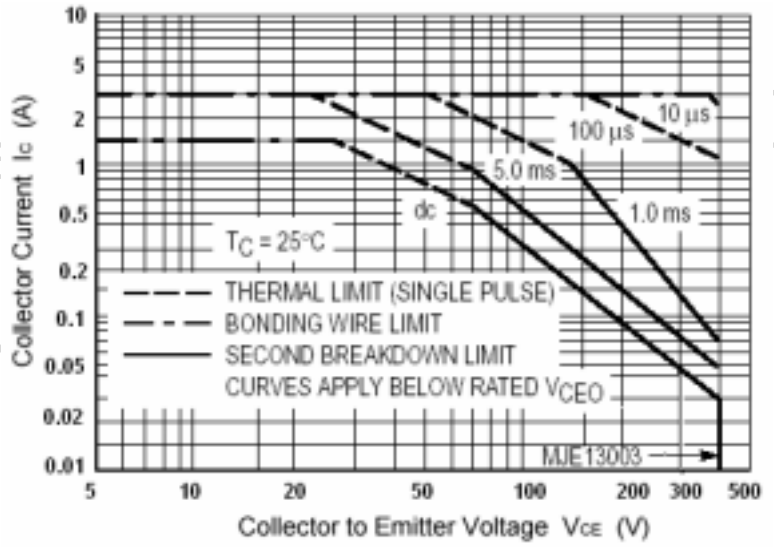

Fig.6 Safe Operating Area